General Description

The WSF30P04 is the highest performance trench P-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSF30P04 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

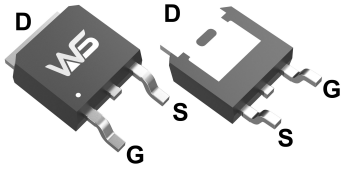
Product Summery

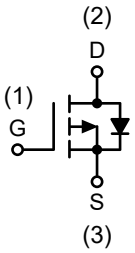
BVDSS	RDSON	ID
-40V	30mΩ	-24A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

TO-252-2L Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ -10V[1]	-24	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ -10V[1]	-18	A
I_{DM}	Pulsed Drain Current[2]	-30	A
I_{AR}	Avalanche Current	-24	A
EAR	Repetitive avalanche energy L=0.1mH	30	mJ
EAS	Single pulse avalanche energy L=0.3mH	60	mJ
P_D@T_C=25℃	Total Power Dissipation[4]	50	W
P_D@T_C=100℃	Total Power Dissipation[4]	25	W
P_D@T_A=25℃	Power Dissipation [A]	2.5	W
P_D@T_A=70℃	Power Dissipation [A]	1.6	W
T_J T_{STG}	Junction and Storage Temperature Range	-55 to 175	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	50	℃/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1] (t ≤10s)	---	25	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	2.5	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-40	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.0232	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-12A	---	30	38	mΩ
		V_{GS}=-4.5V , I_D=-8A	---	46	59	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.8	-1.9	-3.0	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.6	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-32V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-32V , V_{GS}=0V , T_J=55℃	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-12A	---	16	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	6.5	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-20V , V_{GS}=-10V , I_D=-12A	---	7	---	nC
Q_{gs}	Gate-Source Charge		---	2.2	---	
Q_{gd}	Gate-Drain Charge		---	2.4	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-20V , V_{GS}=-10V , R_G=3.0Ω I_D=-12A	---	8	---	ns
T_r	Rise Time		---	12.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	24	---	
T_f	Fall Time		---	12.5	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	657	850	pF
C_{oss}	Output Capacitance		---	143	185	
C_{rss}	Reverse Transfer Capacitance		---	63	60	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	-12	A
I_{SM}	Pulsed Source Current[2,6]		---	---	-24	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1	V
t_{rr}	Reverse Recovery Time	IF=-12A,dI/dt=100A/μs,		23.2	---	nS
Q_{rr}	Reverse Recovery Charge		---	18.2	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper,t<10sec.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.1mH,I_{AR}=-12A
4.The power dissipation is limited by 150℃ junction temperature
5.The Min. value is 100% EAS tested guarantee.
6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

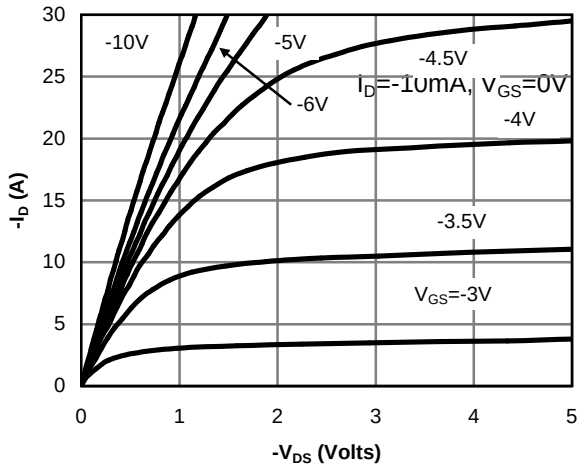


Fig 1: On-Region Characteristics

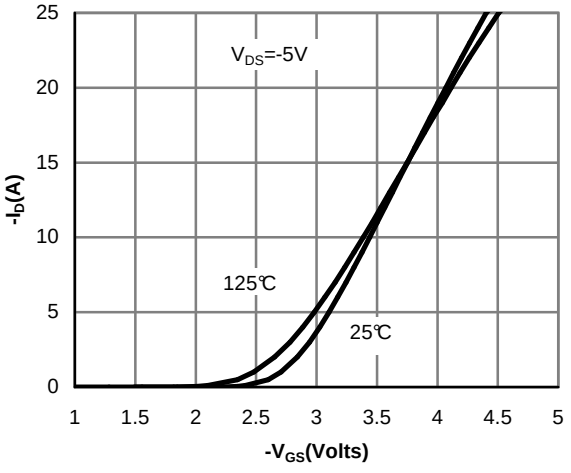


Figure 2: Transfer Characteristics

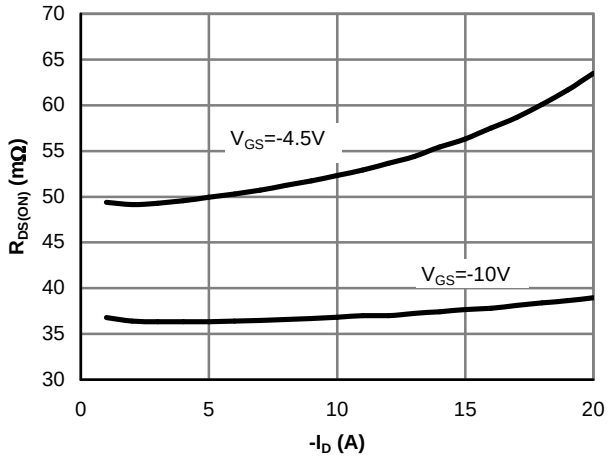


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

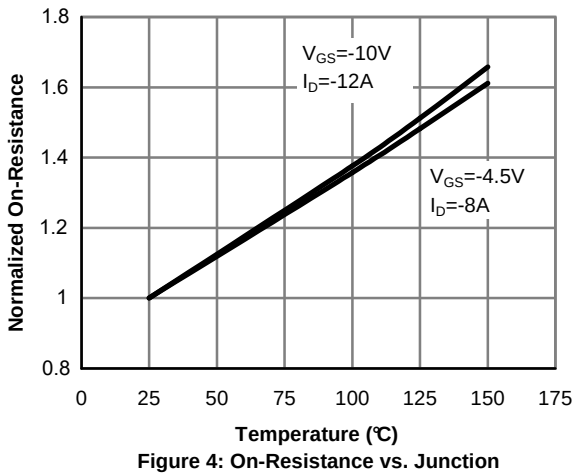


Figure 4: On-Resistance vs. Junction Temperature

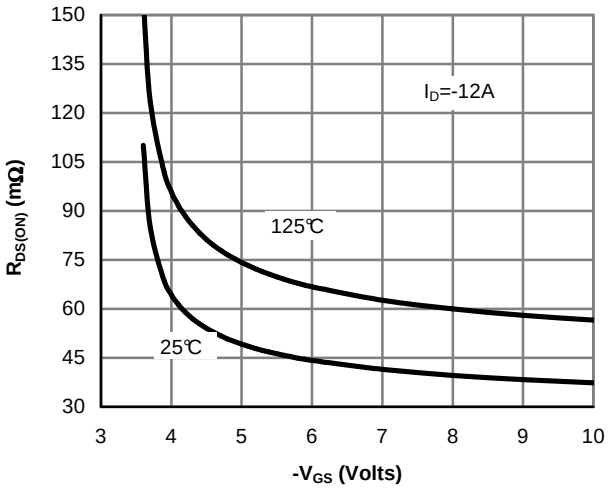


Figure 5: On-Resistance vs. Gate-Source Voltage

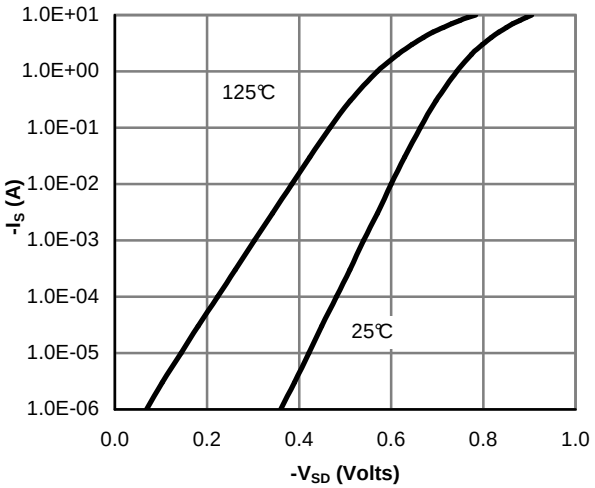


Figure 6: Body-Diode Characteristics

Typical Characteristics

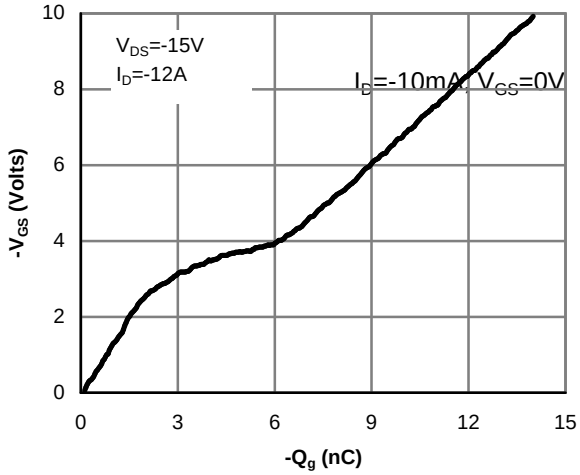


Figure 7: Gate-Charge Characteristics

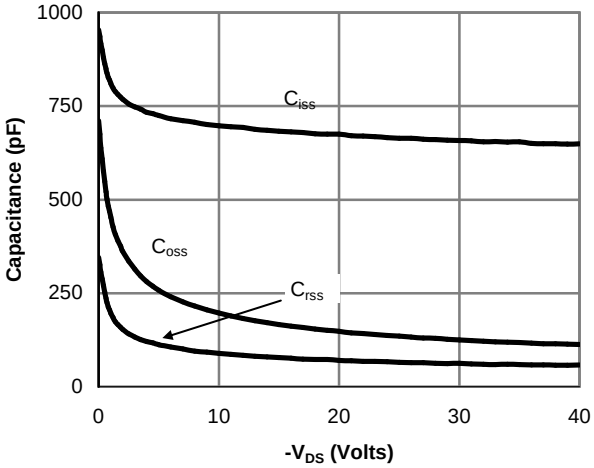


Figure 8: Capacitance Characteristics

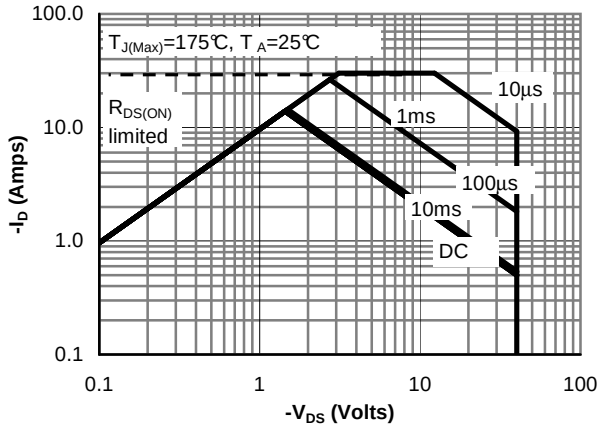


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

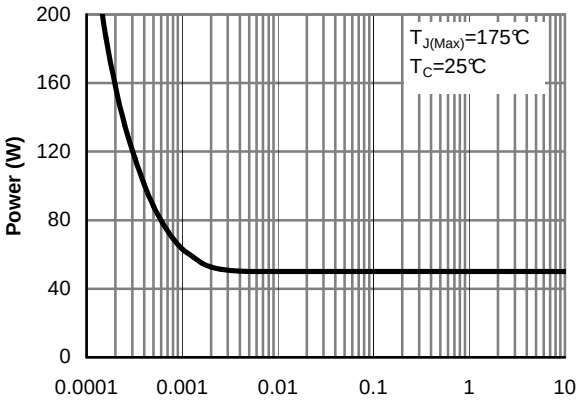


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

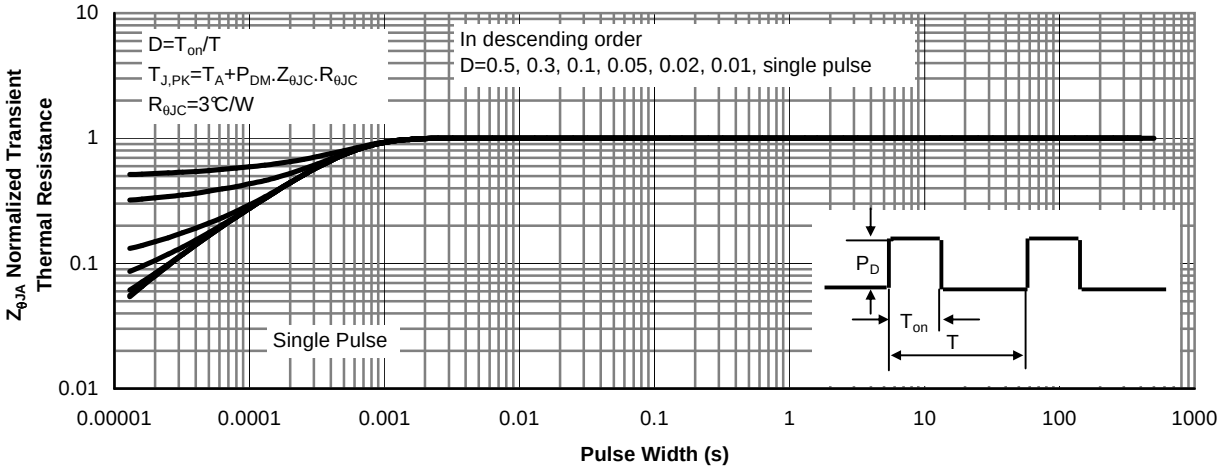


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Typical Characteristics

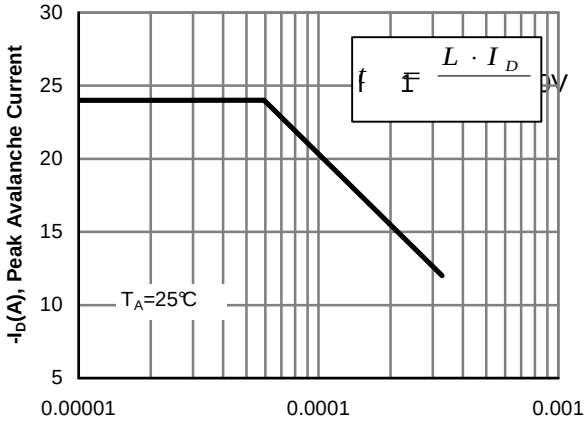


Figure 12: Single Pulse Avalanche capability

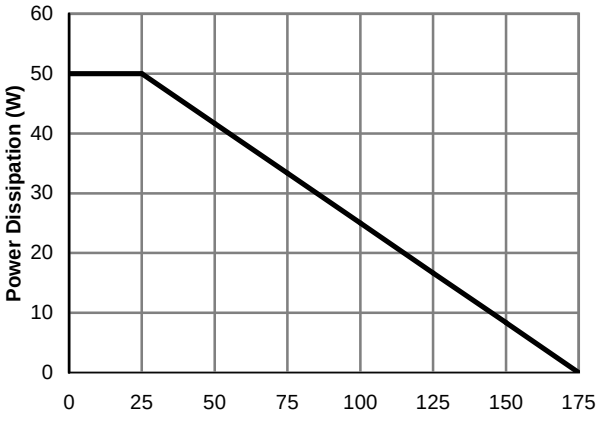


Figure 13: Power De-rating (Note B)

850

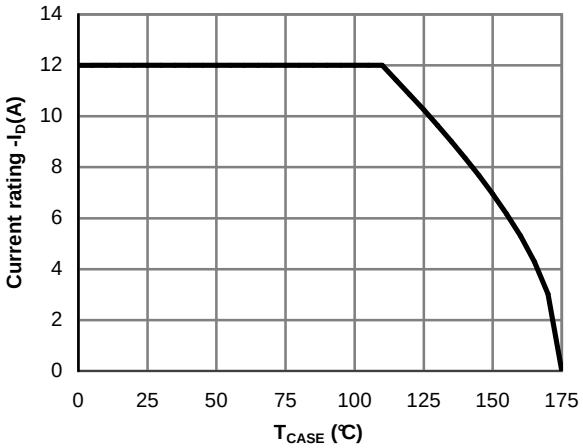


Figure 14: Current De-rating (Note B)

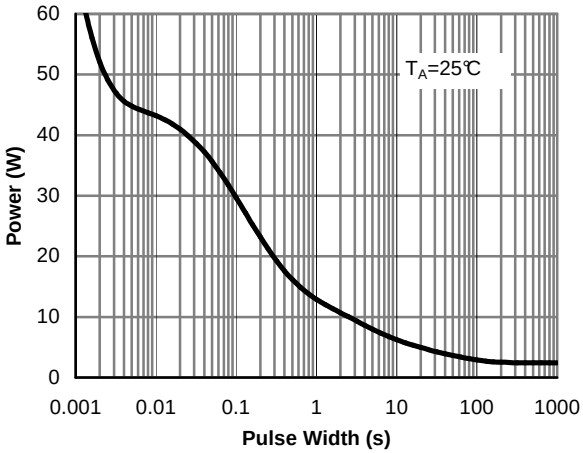


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

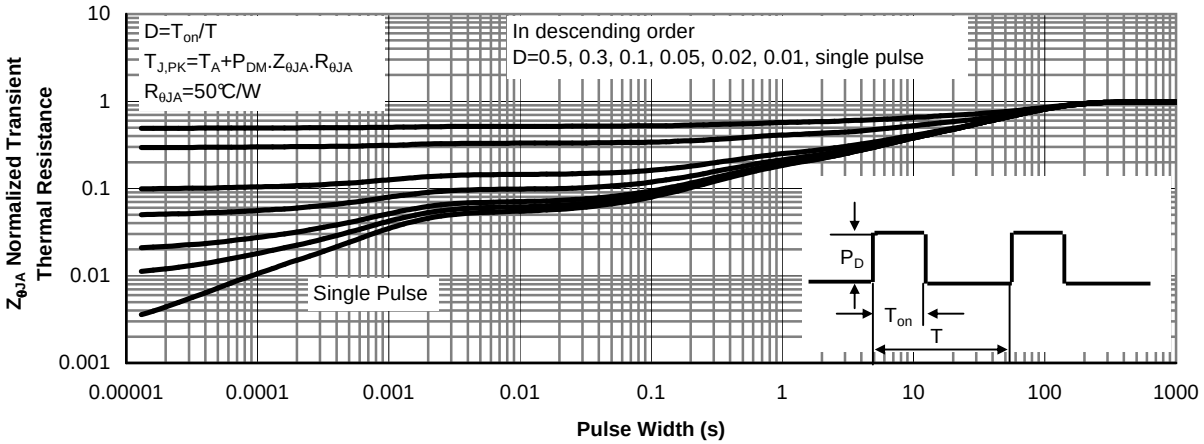
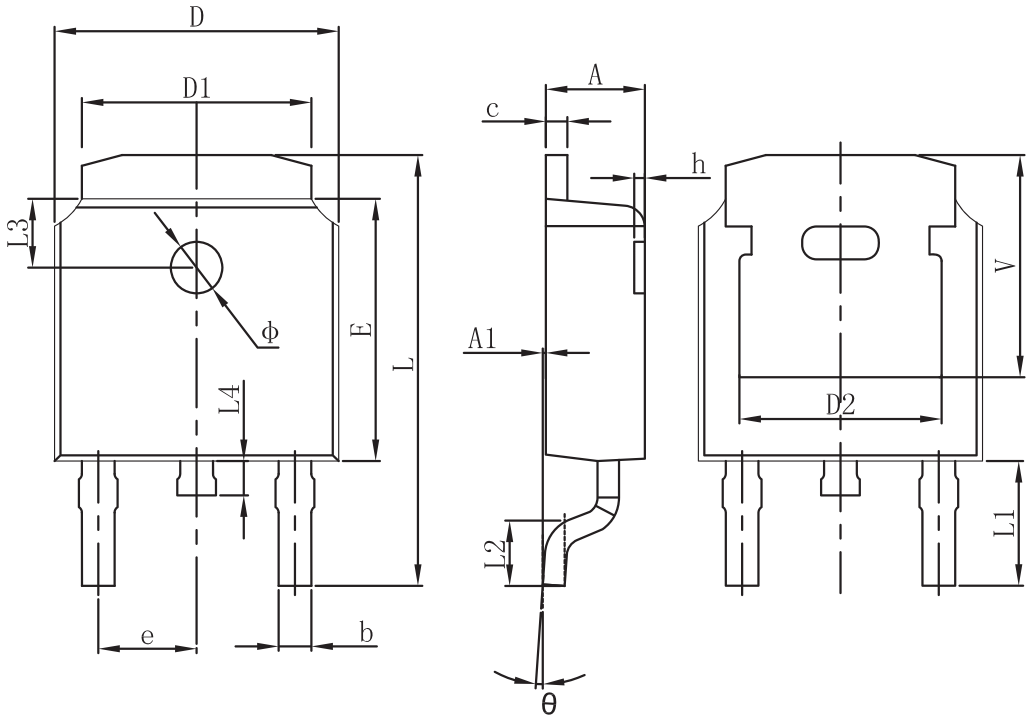


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

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